SPICE Device Model SiSA01DN



Vishay Siliconix

P-Channel 30 V (D-S) MOSFET

DESCRIPTION

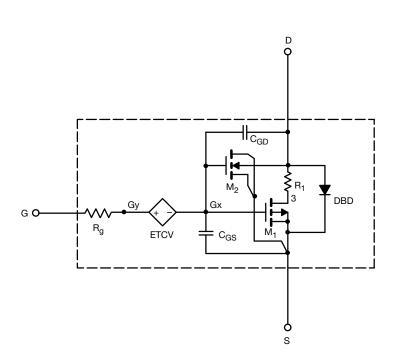
The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched $C_{gd}\xspace$ model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- P-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- Apply for both linear and switching application
- Accurate over the -55 °C to 125 °C temperature range
- · Model the gate charge

SUBCIRCUIT MODEL SCHEMATIC



Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits



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| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | |
|--|---------------------|--|-------------------|------------------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS | SIMULATED DATA | MEASURED DATA | UNIT |
| Static | | | | | |
| Gate threshold voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = -250 \ \mu A$ | 1.8 | - | V |
| Drain-source on-state resistance ^a | Р | $V_{GS} = -10 \text{ V}, \text{ I}_{D} = -15 \text{ A}$ | 0.0042 | 0.0041 | Ω |
| | R _{DS(on)} | $V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}$ | 0.0067 | 0.0063 | |
| Forward transconductance ^a | 9 _{fs} | V _{DS} = -15 V, I _D = -15 A | 59 | 81 | S |
| Diode forward voltage | V _{SD} | I _S = -5 A | -0.73 | -0.73 | V |
| Dynamic ^b | | | | | |
| Input capacitance | C _{iss} | V_{DS} = -15 V, V_{GS} = 0 V, f = 1 MHz | 3680 | 3490 | pF |
| Output capacitance | C _{oss} | | 1490 | 1420 | |
| Reverse transfer capacitance | C _{rss} | | 160 | 70 | |
| Total gate charge | 0 | $V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}$ | 53 | 56 | nC |
| | Qg | $V_{DS} = -15 \text{ V}, \text{ V}_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -10 \text{ A}$ | 26 | 27 | |
| Gate-source charge | Q _{gs} | | 9.4 | 9.4 | |
| Gate-drain charge | Q _{gd} | | 8 | 8.2 | |

Notes

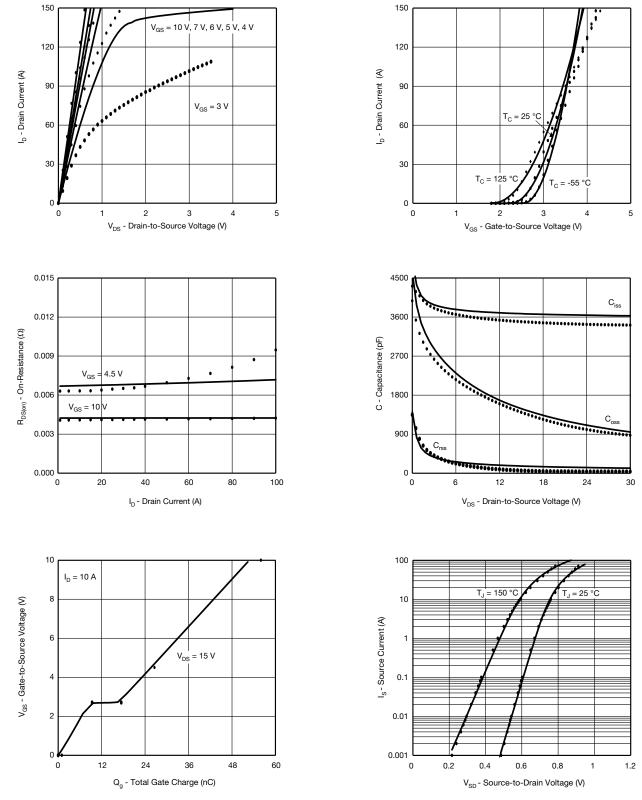
a. Pulse test; pulse width $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%$

b. Guaranteed by design, not subject to production testing



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COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)



Note

• Dots and squares represent measured data Copyright: Vishay Intertechnology, Inc.

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